

# Lin Wang

## List of Publications by Year in descending order

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Version: 2024-02-01

35  
papers

1,744  
citations

279778

23  
h-index

395678

33  
g-index

35  
all docs

35  
docs citations

35  
times ranked

2519  
citing authors

#	ARTICLE	IF	CITATIONS
1	Data-driven discovery of high performance layered van der Waals piezoelectric NbOI <sub>2</sub> . Nature Communications, 2022, 13, 1884.	12.8	22
2	Exploring Low Power and Ultrafast Memristor on p-Type van der Waals SnS. Nano Letters, 2021, 21, 8800-8807.	9.1	57
3	Electron tunneling at the molecularly thin 2D perovskite and graphene van der Waals interface. Nature Communications, 2020, 11, 5483.	12.8	35
4	Exploring Ferroelectric Switching in $\text{In}_2\text{Se}_3$ for Neuromorphic Computing. Advanced Functional Materials, 2020, 30, 2004609.	14.9	119
5	Zero-bias mid-infrared graphene photodetectors with bulk photoresponse and calibration-free polarization detection. Nature Communications, 2020, 11, 6404.	12.8	111
6	A van der Waals Synaptic Transistor Based on Ferroelectric $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ and 2D Tungsten Disulfide. Advanced Electronic Materials, 2020, 6, 2000057.	5.1	68
7	In-Plane Ferroelectric Tin Monosulfide and Its Application in a Ferroelectric Analog Synaptic Device. ACS Nano, 2020, 14, 7628-7638.	14.6	106
8	Site-selective alkene borylation enabled by synergistic hydrometallation and borometallation. Nature Catalysis, 2020, 3, 585-592.	34.4	60
9	Single crystal of a one-dimensional metallo-covalent organic framework. Nature Communications, 2020, 11, 1434.	12.8	77
10	A Compact Model for 2-D Poly-MoS <sub>2</sub> FETs With Resistive Switching in Postsynaptic Simulation. IEEE Transactions on Electron Devices, 2019, 66, 4092-4100.	3.0	4
11	Anomalous Broadband Spectrum Photodetection in 2D Rhenium Disulfide Transistor. Advanced Optical Materials, 2019, 7, 1901115.	7.3	37
12	A Fully Printed Flexible MoS <sub>2</sub> Memristive Artificial Synapse with Femtojoule Switching Energy. Advanced Electronic Materials, 2019, 5, 1900740.	5.1	123
13	Unipolar n-Type Conduction in Black Phosphorus Induced by Atomic Layer Deposited MgO. IEEE Electron Device Letters, 2019, 40, 471-474.	3.9	9
14	Electronic Devices and Circuits Based on Wafer-Scale Polycrystalline Monolayer MoS <sub>2</sub> by Chemical Vapor Deposition. Advanced Electronic Materials, 2019, 5, 1900393.	5.1	57
15	Fabry-Perot cavity enhanced light-matter interactions in two-dimensional van der Waals heterostructure. Nano Energy, 2019, 62, 667-673.	16.0	35
16	Artificial Synapses Based on Multiterminal Memtransistors for Neuromorphic Application. Advanced Functional Materials, 2019, 29, 1901106.	14.9	192
17	Recent Advances in Black Phosphorus-Based Electronic Devices. Advanced Electronic Materials, 2019, 5, 1800666.	5.1	31
18	2D Photovoltaic Devices: Progress and Prospects. Small Methods, 2018, 2, 1700294.	8.6	135

#	ARTICLE	IF	CITATIONS
19	A Black Phosphorus Carbide Infrared Phototransistor. <i>Advanced Materials</i> , 2018, 30, 1705039.	21.0	95
20	Pronounced Photovoltaic Effect in Electrically Tunable Lateral Black Phosphorus Heterojunction Diode. <i>Advanced Electronic Materials</i> , 2018, 4, 1700442.	5.1	27
21	A Surface Potential- and Physics- Based Compact Model for 2D Polycrystalline-MoS <sub>2</sub> /FET with Resistive Switching Behavior in Neuromorphic Computing. , 2018, , .		1
22	Resolving ZnO-based coaxial core-multishell heterostructure by electrical scanning probe microscopy. <i>Applied Physics Letters</i> , 2018, 113, 222103.	3.3	1
23	High Mobility Anisotropic Black Phosphorus Nanoribbon Field-Effect Transistor. <i>Advanced Functional Materials</i> , 2018, 28, 1801524.	14.9	77
24	Black Phosphorus Carbide as a Tunable Anisotropic Plasmonic Metasurface. <i>ACS Photonics</i> , 2018, 5, 3116-3123.	6.6	58
25	Gigahertz Integrated Circuits Based on Complementary Black Phosphorus Transistors. <i>Advanced Electronic Materials</i> , 2018, 4, 1800274.	5.1	23
26	Tunable black phosphorus heterojunction transistors for multifunctional optoelectronics. <i>Nanoscale</i> , 2018, 10, 14359-14367.	5.6	24
27	Complementary Black Phosphorus Nanoribbons Field-Effect Transistors and Circuits. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 4122-4128.	3.0	14
28	Efficient and reliable surface charge transfer doping of black phosphorus via atomic layer deposited MgO toward high performance complementary circuits. <i>Nanoscale</i> , 2018, 10, 17007-17014.	5.6	34
29	Investigation of tip-depletion-induced fail in scanning capacitance microscopy for the determination of carrier type. <i>Ultramicroscopy</i> , 2017, 174, 46-49.	1.9	5
30	Infrared Black Phosphorus Phototransistor with Tunable Responsivity and Low Noise Equivalent Power. <i>ACS Applied Materials &amp; Interfaces</i> , 2017, 9, 36130-36136.	8.0	73
31	Black phosphorus carbide infrared phototransistor with wide spectrum sensing for IoT applications. , 2017, , .		0
32	Characterization of carrier concentration in ZnO nanowires by scanning capacitance microscopy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016, 13, 576-580.	0.8	9
33	Cross-section imaging and p-type doping assessment of ZnO/ZnO:Sb core-shell nanowires by scanning capacitance microscopy and scanning spreading resistance microscopy. <i>Applied Physics Letters</i> , 2016, 109, .	3.3	9
34	Access to residual carrier concentration in ZnO nanowires by calibrated scanning spreading resistance microscopy. <i>Applied Physics Letters</i> , 2016, 108, .	3.3	10
35	Nanoscale calibration of n-type ZnO staircase structures by scanning capacitance microscopy. <i>Applied Physics Letters</i> , 2015, 107, .	3.3	6